

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N4001GPP SERIES

GLASS PASSIVATED JUNCTION
SILICON RECTIFIER
1.0 AMP, 50 THRU 1000 VOLTS

JEDEC DO-41 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N4001GPP Series types are 1.0 Amp Glass Passivated Junction Silicon Rectifiers which are high quality, well constructed, highly reliable components designed for use in all types of military, commercial, industrial, entertainment, computer, and automotive applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

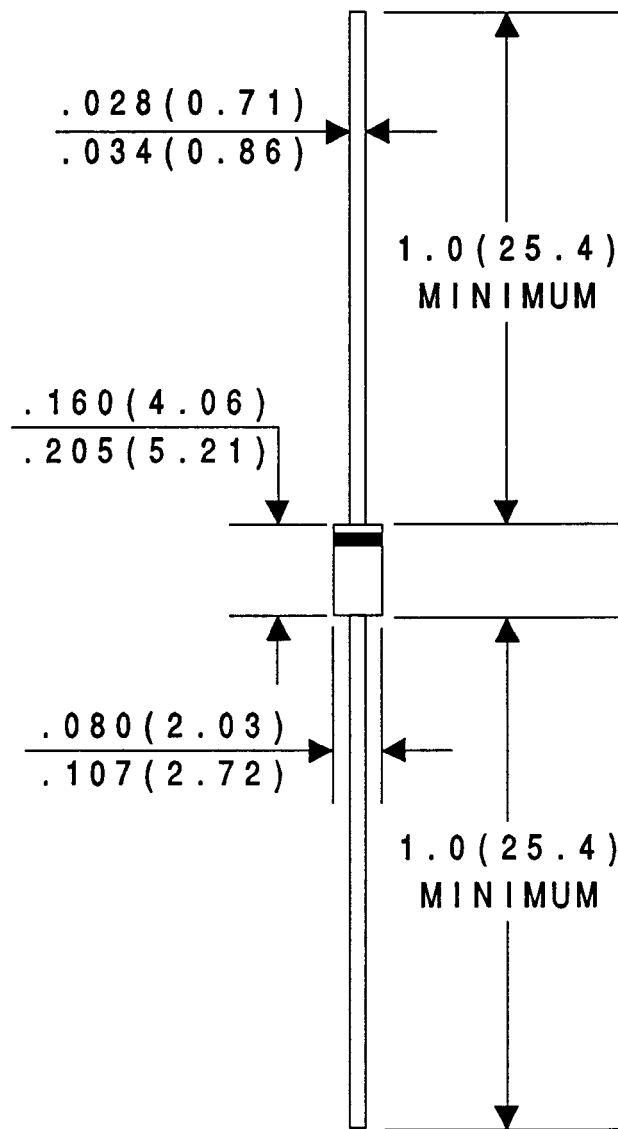
	SYMBOL	1N4001 GPP	1N4002 GPP	1N4003 GPP	1N4004 GPP	1N4005 GPP	1N4006 GPP	1N4007 GPP	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Forward Current									
@ $T_A = 75^\circ\text{C}$	I_O				1.0				A
Peak Forward Surge Current	I_{FSM}				30				A
Operating and Storage									
Junction Temperature	T_J, T_{stg}				-65 to +175				$^\circ\text{C}$
Thermal Resistance	θ_{JA}				45				$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_F	$I_F = 1.0\text{A}$			1.1	V
I_R	$V_R = \text{Rated } V_{RRM}$			5.0	μA
I_R	$V_R = \text{Rated } V_{RRM}, T_A = 125^\circ\text{C}$			50	μA
t_{rr}	$I_F = 0.5\text{A}, I_R = 1.0\text{A}, I_{rr} = 0.25\text{A}$			2.0	μs
C_J	$V_R = 4.0\text{V}, f = 1.0\text{MHz}$		8.0		pF

(SEE REVERSE FOR MECHANICAL OUTLINE)

JEDEC DO-41 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).